

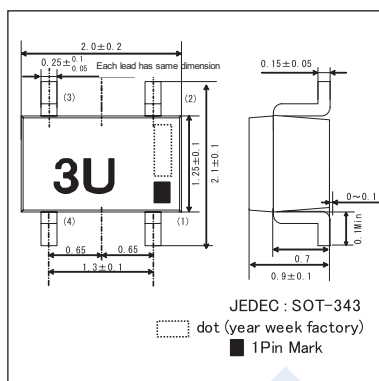
Schottky Diodes

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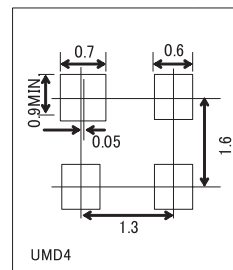
■ Features

- Ultra small mold type.
- LowV_F
- High reliability

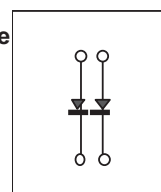
●External dimensions (Unit : mm)



●Land size figure (Unit : mm)



●Structure



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	V _{RM}	30	V
Reverse voltage (DC)	V _R	30	
Average rectified forward current (*1)	I _O	200	mA
Forward current surge peak (60Hz.1cyc) (*1)	I _{FSM}	1	A
Junction Temperature	T _J	125	°C
Storage Temperature range	T _{stg}	-40 to +125	

(*1) Rating of per diode

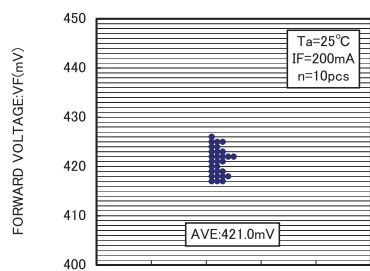
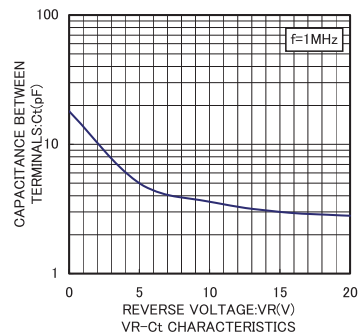
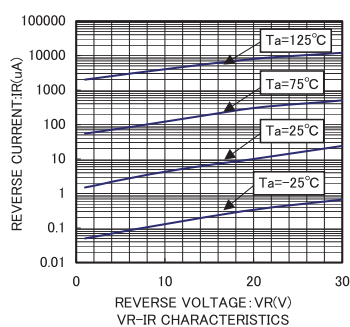
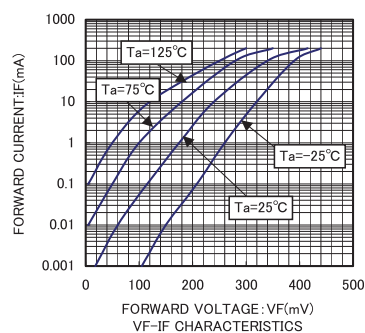
■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V _R	I _R = 100 μA	30			V
Forward voltage	V _{F1}	I _F = 1mA			0.28	
	V _{F2}	I _F = 10mA			0.33	
	V _{F3}	I _F = 100mA			0.43	
	V _{F4}	I _F = 200mA			0.50	
Reverse current	I _R	V _R = 10 V			30	μA

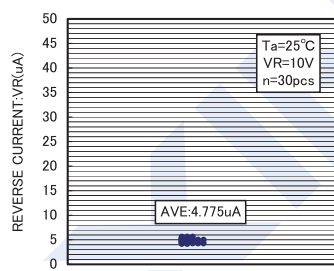
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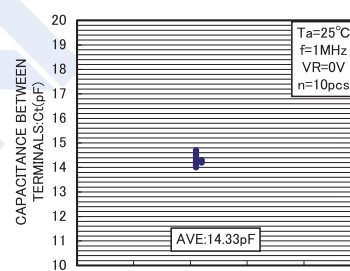
■ Electrical characteristic curves (Ta=25°C)



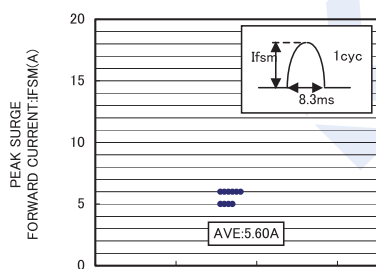
VF DISPERSION MAP



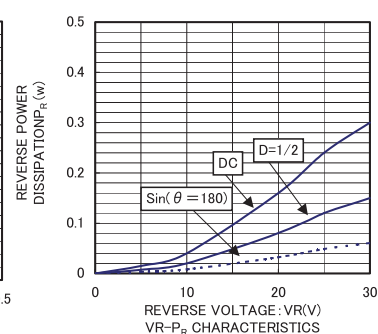
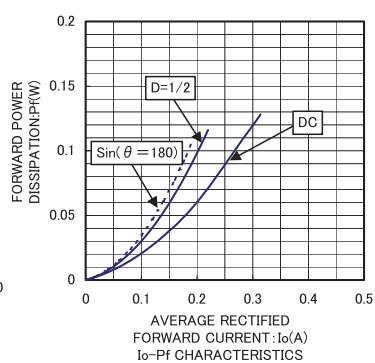
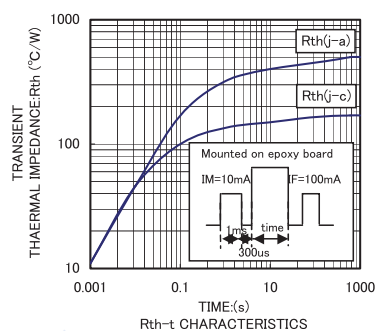
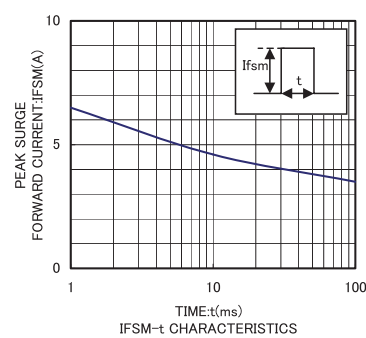
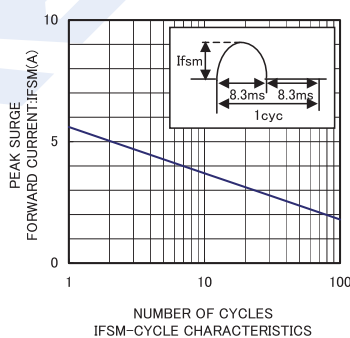
IR DISPERSION MAP



Ct DISPERSION MAP



IFSM DISPERSION MAP



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